

IN THE CLAIMS

Please amend the claims as follows:

1. (Original) A semiconductor single crystal manufacturing apparatus, comprising a chamber disposed in a furnace and having a crucible in which a melt is charged, a heater for heating the crucible, and a wire disposed within the chamber, wherein:
at least a region of the wire which is exposed to a high temperature is covered with a collar.
2. (Original) The semiconductor single crystal manufacturing apparatus according to claim 1, wherein the collar is disposed in plural.
3. (Original) The semiconductor single crystal manufacturing apparatus according to claim 1 or 2, wherein the collar is disposed between a wire winding device and a seed crystal.
4. (Original) The semiconductor single crystal manufacturing apparatus according to any one of claims 1 through 3, wherein the collar is disposed closely to cover the wire.

5. (Presently Amended) A ~~The~~ semiconductor single crystal manufacturing apparatus according to claim 1, ~~comprising a chamber disposed in a furnace and having a crucible in which a melt is charged, a pull chamber disposed above the chamber, a wherein the wire having a region covered with the collar hangs a seed holder, which is vertically moved between within the chamber, an inside of the pull chamber and the chamber, and a wire which hangs the seed holder via a coupling member, and wherein:~~ a length of at least either of the seed holder or the coupling member is determined to be a length to locate a proximity of a tip end of the an exposed portion of the wire near a tip end thereof in a region of the wire in a region having a temperature less than a prescribed temperature in a high-temperature atmosphere within the furnace when a the seed crystal is attached to the seed holder and located ~~at a position~~ to come into contact with the melt.

6. (Original) The semiconductor single crystal manufacturing apparatus according to claim 5, wherein less than the prescribed temperature is less than 700°C.